



TITLE: A TRENCHED GATE NON-VOLATILE SEMICONDUCTOR METHOD WITH THE  
SOURCE/DRAIN REGIONS SPACED FROM THE TRENCH BY SIDEWALL DOPINGS  
INVENTOR(S): Yowjuang William Liu and Donald L. Wollesen  
USSN: 09/629,780 Attorney Docket #: AMD-C553397.DIV

1 / 8

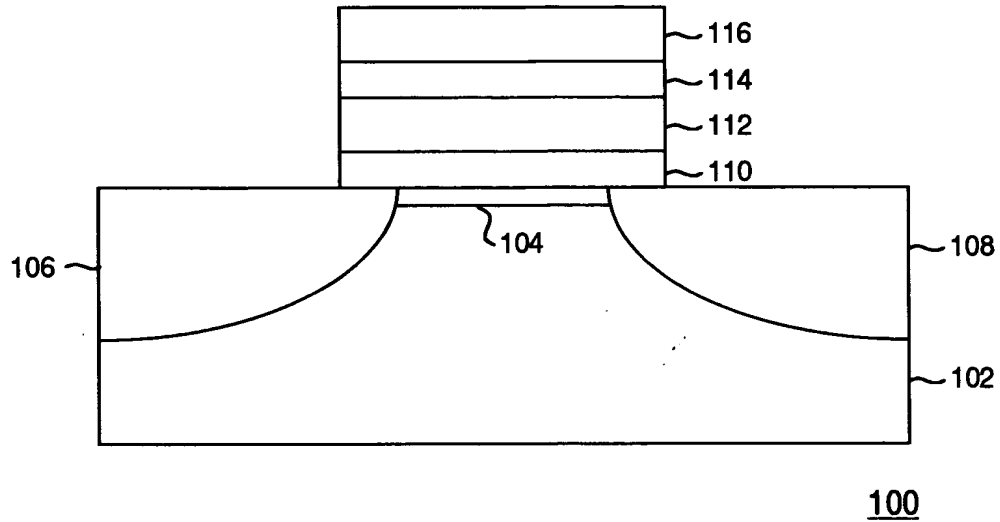


Figure 1 (Prior Art)



### Figure 2A



### Figure 2B

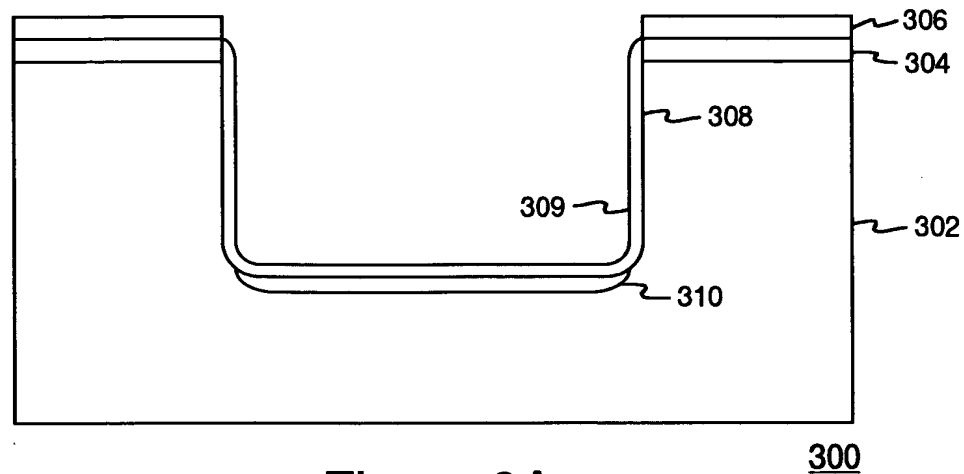


Figure 3A

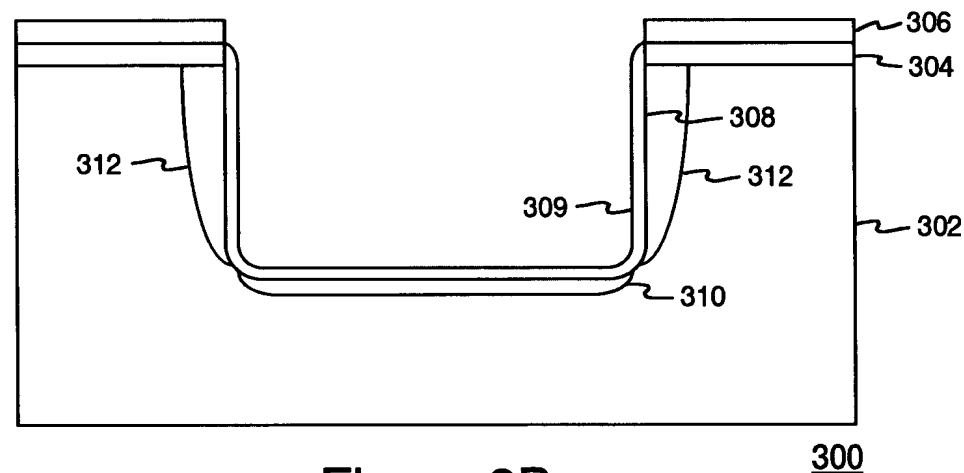


Figure 3B

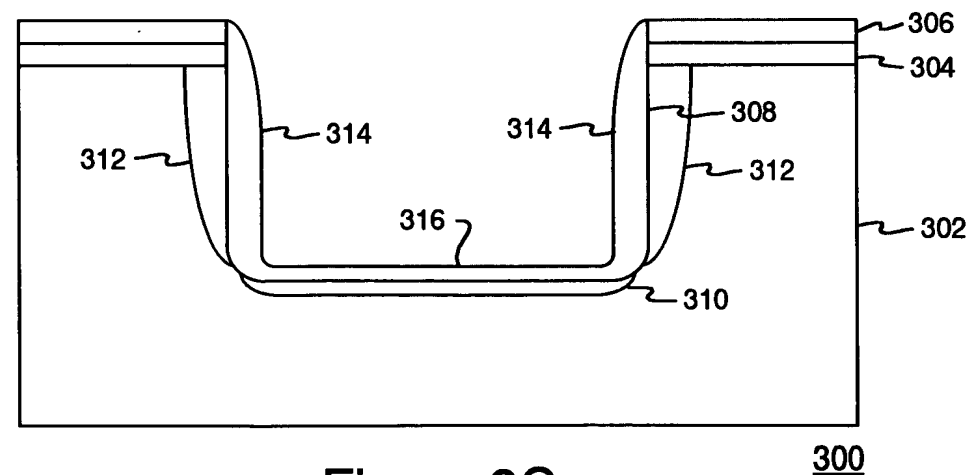


Figure 3C



TITLE: A TRENCHED GATE NON-VOLATILE SEMICONDUCTOR METHOD WITH THE  
SOURCE/DRAIN REGIONS SPACED FROM THE TRENCH BY SIDEWALL DOPINGS  
INVENTOR(S): Yowjuang William Liu and Donald L. Wollesen  
USSN: 09/629,780 Attorney Docket #: AMD-C553397.DIV

4 / 8

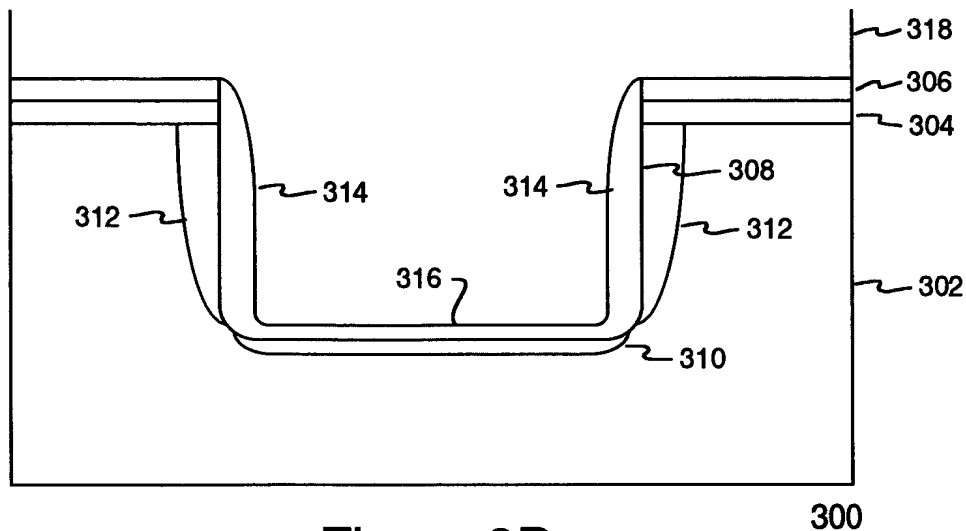


Figure 3D

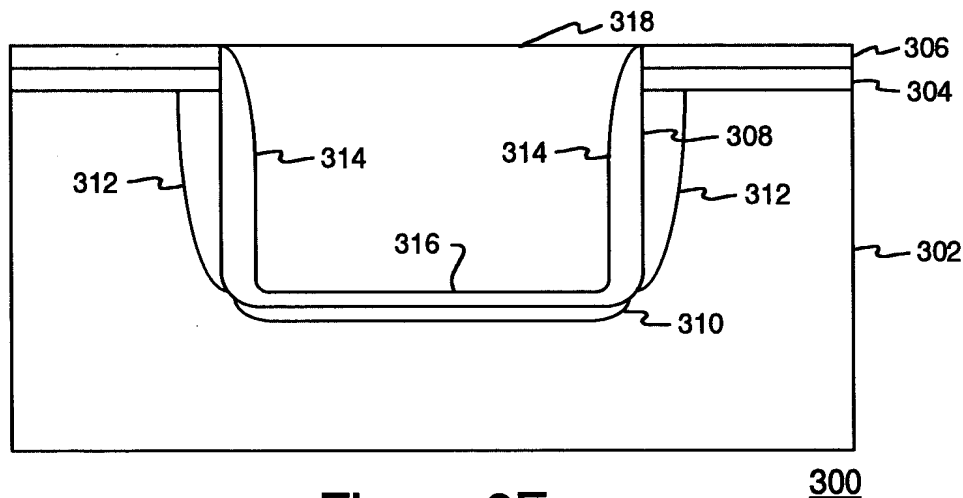


Figure 3E

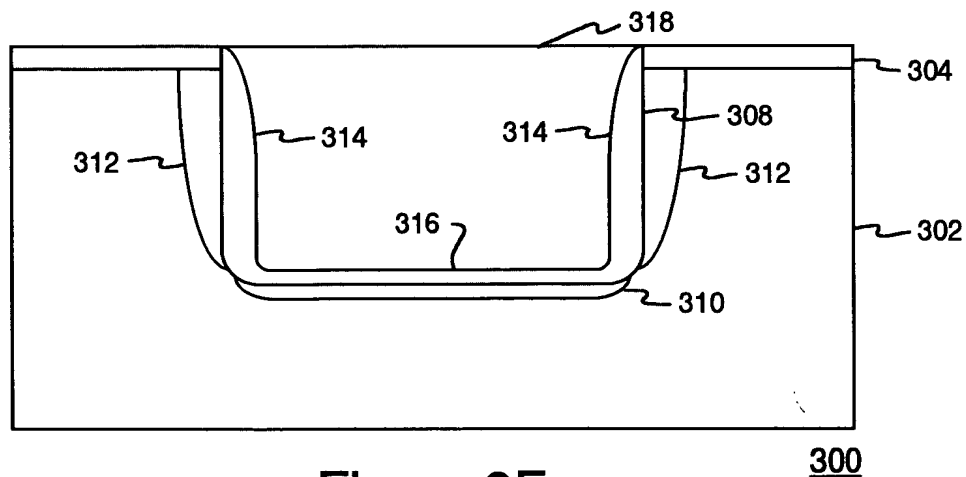


Figure 3F

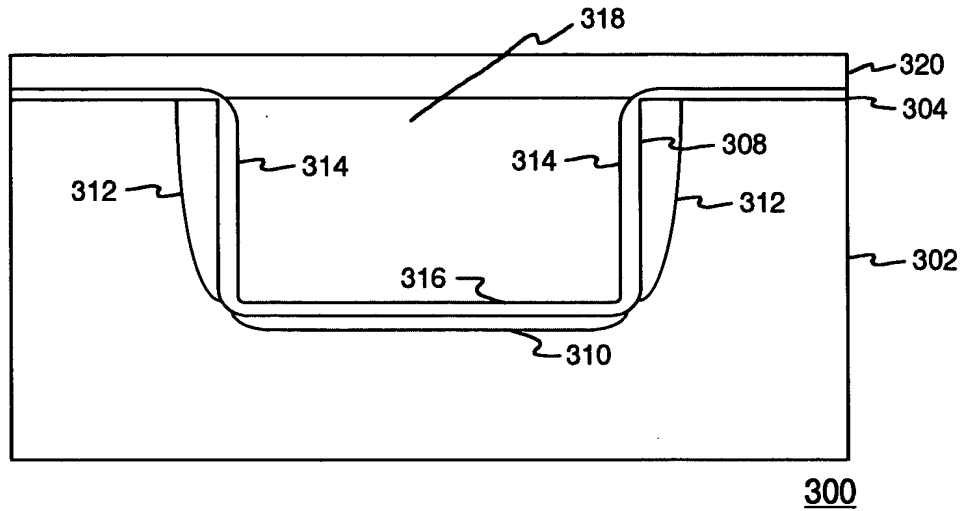


Figure 3G

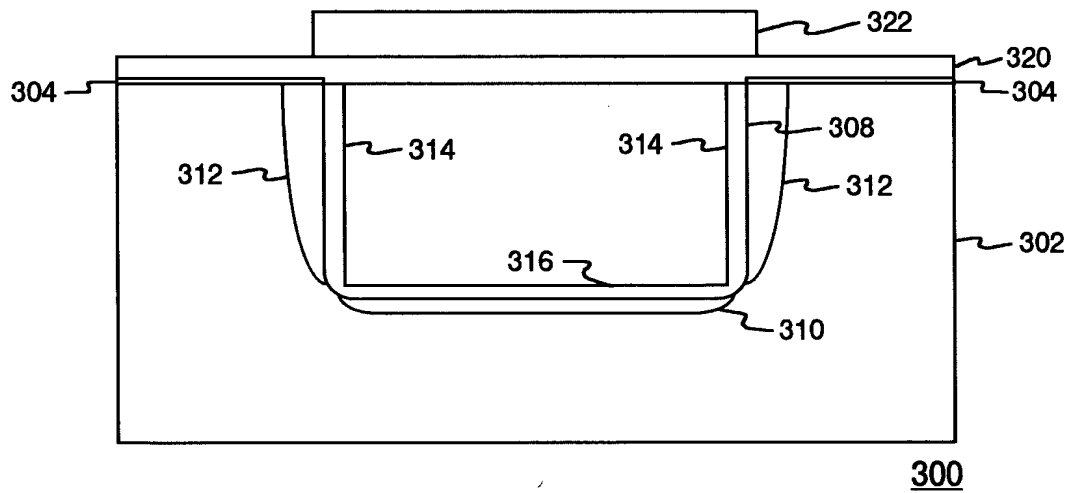


Figure 3H



TITLE: A TRENCHED GATE NON-VOLATILE SEMICONDUCTOR METHOD WITH THE  
SOURCE/DRAIN REGIONS SPACED FROM THE TRENCH BY SIDEWALL DOPINGS  
INVENTOR(S): Yowjuang William Liu and Donald L. Wollesen  
USSN: 09/629,780 Attorney Docket #: AMD-C553397.DIV

6 / 8

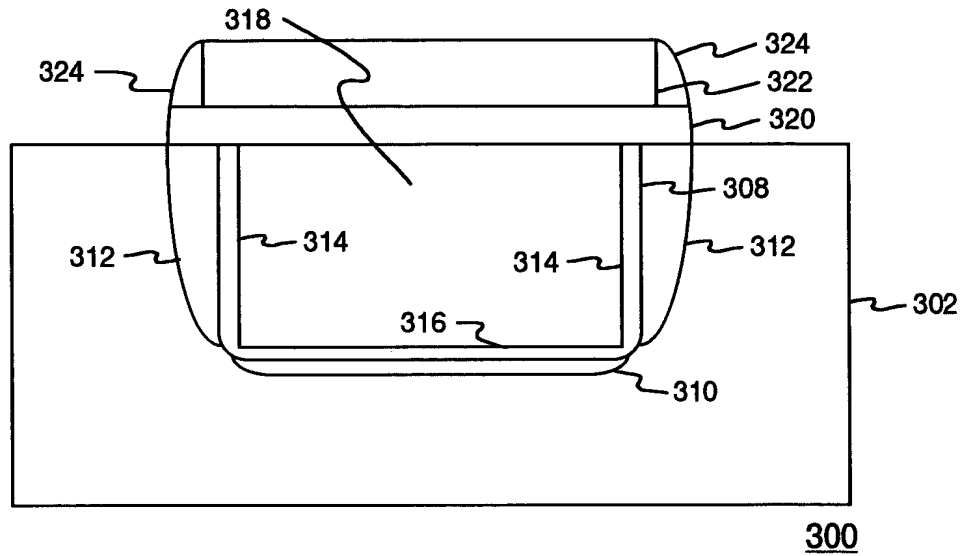


Figure 3I

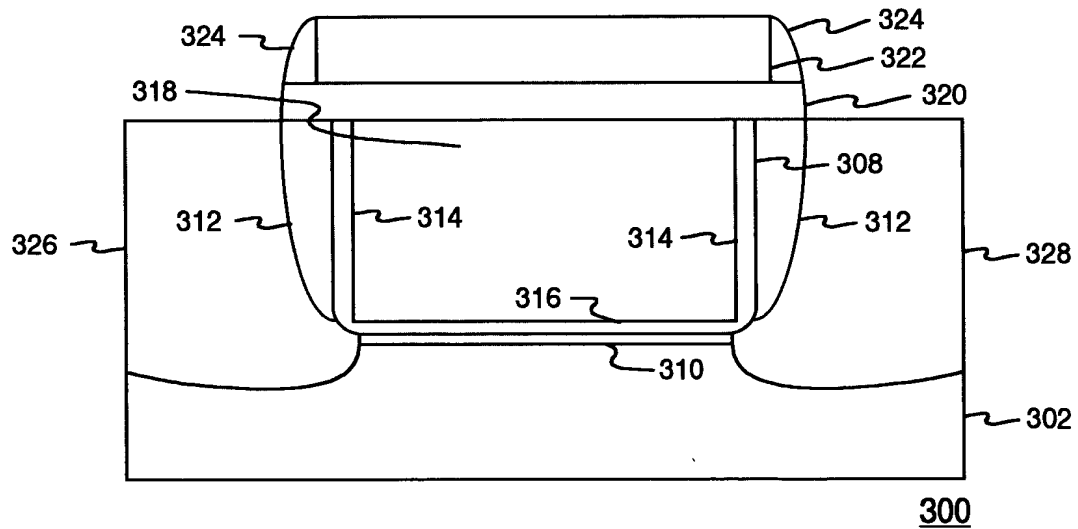
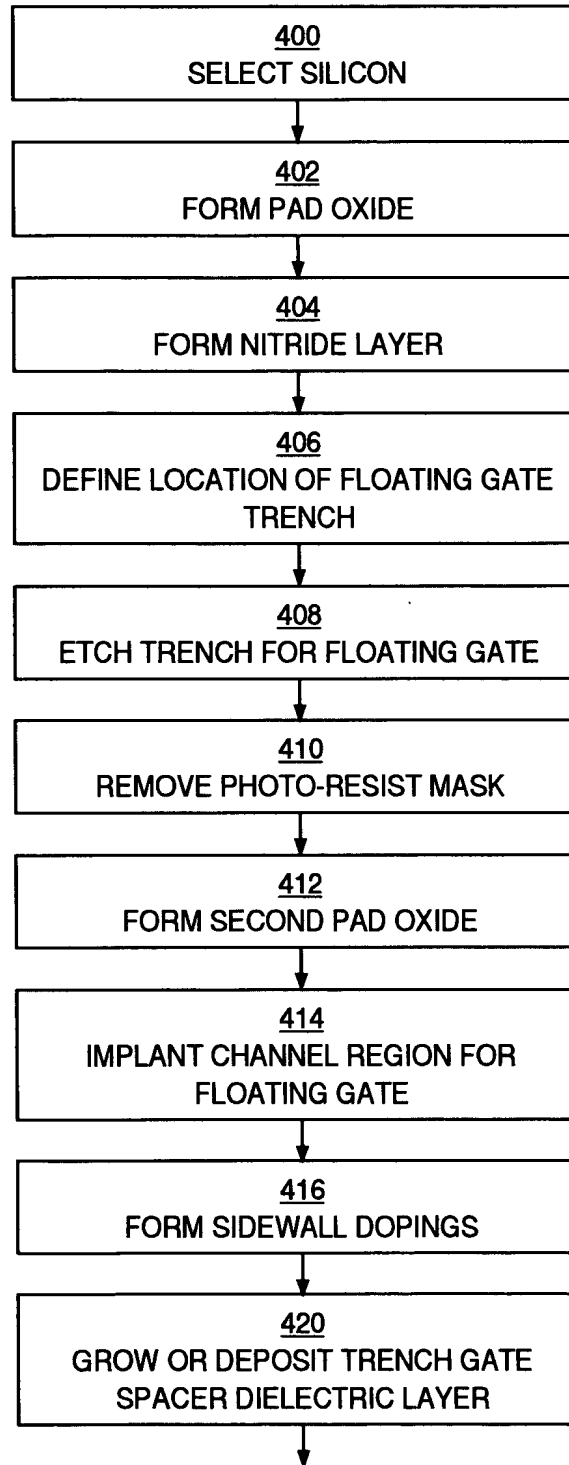


Figure 3J



7 / 8



To Figure 4B

Figure 4A



8 / 8

From Figure 4A

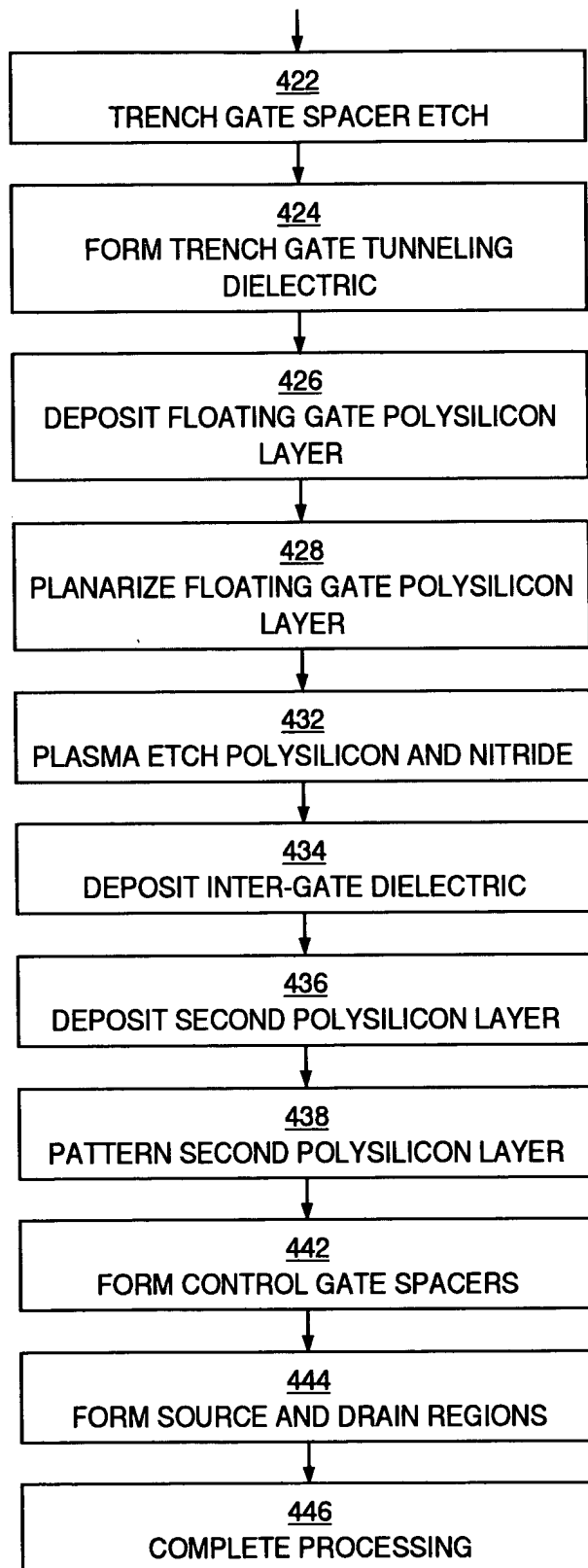


Figure 4B